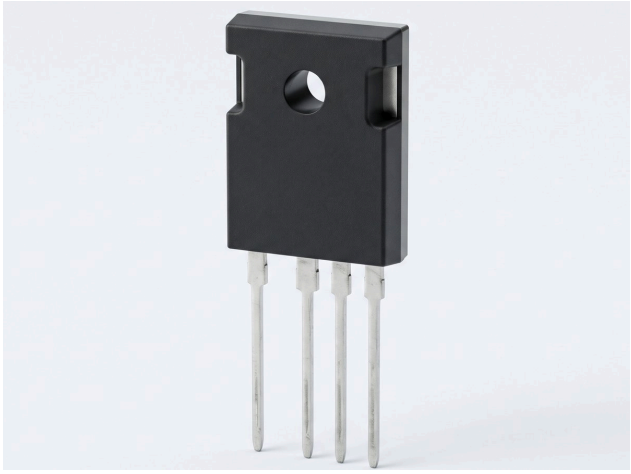
IHSD12R080T4

1200 V, 80 mΩ, Silicon Carbide, Single switch

V_{DSS}	**1200 V**
$R_{DS(on)}$	**80 mΩ**



TO-247-4

Features

- Kelvin-source pin for clean, fast switching
- Through-hole TO-247-4 package

Typical applications

- EV DC fast chargers (PFC and DC-DC)
- Solar inverters and energy storage
- 800 V DC data-center power
- Solid-state transformer cells

Description

1200 V, 80 mΩ silicon-carbide MOSFET in a TO-247-4 package with Kelvin source.

Key specifications

Parameter	Value
V_{DSS}	1200 V
$R_{DS(on)}$ typ., V_{GS} = 18 V, T_{vj} = 25 °C	80 mΩ
I_D, T_C = 25 °C	35 A
Recommended $V_{GS(on)}$	18 V

Full characterization data

Thermal resistance, switching energies and times, capacitances, gate charge and typical characteristic curves for IHSD12R080T4 are available on request: request the full data or write to sales@ironhawksemi.com.

Package

TO-247-4. Mechanical outline drawing, STEP model and PCB footprint available on request.

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Ordering information

Part number	Packing	MOQ	Lead time
IHSD12R080T4	Tube	On request	On request

Information in this document is believed to be accurate but is subject to change without notice. Typical values are not guaranteed. The customer is responsible for validating suitability in the end application. IRONHAWK · sales@ironhawksemi.com

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